

Listing of Claims

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1. (Currently amended) A process comprising:
depositing an undoped transparent oxide semiconductor,
comprising at least one oxide selected from the group consisting of zinc oxide,
indium oxide, tin oxide, and cadmium oxide, in a field effect transistor, by a method
selected from the group consisting of :
 - a) physical vapor deposition of an undoped transparent oxide semiconductor
in an ~~effective partial pressure of oxygen mixed with~~ a controlled partial
pressure of 0.1 P_c to 10 P_c , in an inert gas;
 - b) resistive evaporation of an undoped transparent oxide semiconductor in an
effective partial pressure of oxygen;
 - c) laser evaporation of an undoped transparent oxide semiconductor in an
~~effective partial pressure of oxygen mixed with~~ a controlled partial
pressure of 0.1 P_c to 10 P_c , in an inert gas;
 - d) electron beam evaporation of an undoped transparent oxide
semiconductor in an ~~effective partial pressure of oxygen mixed with~~ a
controlled partial pressure of 0.1 P_c to 10 P_c , in an inert gas; and
 - e) chemical vapor deposition of an undoped transparent oxide semiconductor
in an ~~effective partial pressure of oxygen mixed with~~ a controlled partial
pressure of 0.1 P_c to 10 P_c , in an inert gas.
2. (Previously presented) The process of Claim 1 wherein the physical vapor
deposition is rf magnetron sputtering.
3. (Previously presented) The process of Claim 1 wherein the physical vapor
deposition is dc magnetron sputtering.

4. (Previously presented) The process of Claim 1 wherein the physical vapor deposition is diode sputtering.
5. (Previously presented) The process of Claim 1 wherein the physical vapor deposition is triode sputtering.
6. (Previously presented) The process of Claim 1 wherein the physical vapor deposition is ion beam sputtering.
7. (Original) The process of any of claims 1(a), 2, 3, 4, 5 or 6 wherein deposition is by physical vapor deposition and wherein the inert gas is selected from the group consisting of helium, neon, argon, krypton, and xenon.
8. (Original) The process of Claim 1(e) wherein the chemical vapor deposition is low pressure chemical vapor deposition.
9. (Original) The process of Claim 1(e) wherein the chemical vapor deposition is plasma-enhanced chemical vapor deposition.
10. (Original) The process of Claim 1(e) wherein the chemical vapor deposition is laser-enhanced chemical vapor deposition.
11. (Previously presented) The process of Claim 1(e) wherein the chemical vapor deposition is atomic layer chemical vapor deposition.
12. (Cancelled)
13. (Currently amended) The process of ~~any one of claims~~ claim 1 to 14 wherein the effective partial pressure of oxygen is between 0.5 and 2 times the critical pressure.
- 14-24. (Cancelled)